

PATENT ABSTRACTS OF JAPAN

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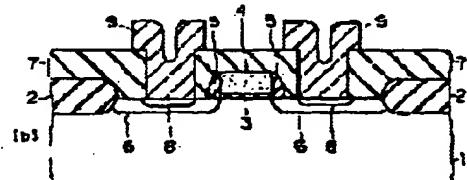
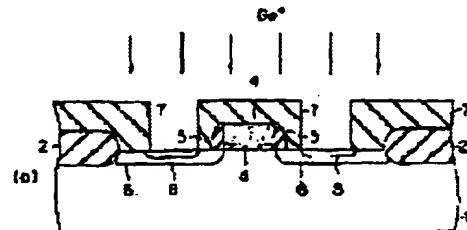
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(54) SEMICONDUCTOR DEVICE AND FABRICATION THEREOF

(57)Abstract:

PURPOSE: To provide a semiconductor device wherein contact resistance is not increased even though the device is made finer.

CONSTITUTION: There are provided on a silicon substrate 1 a gate electrode 4 formed through a gate oxide film 3, a source-drain diffusion layer 6 formed on the surface of the silicon substrate 1 oppositely to the gate electrode 4, a source-drain electrode 9 formed on the source-drain diffusion layer 6, and a Si-Ge mixed crystal layer 8 displaced between the source-drain electrode 9 and the source-drain diffusion layer 6.



LEGAL STATUS

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